

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-9 (Canceled).

Claim 10 (Previously Presented): A method according to claim 18, wherein the fastening includes a bonding chosen from bonding by molecular adhesion via intermediate films or without intermediate films, bonding by reaction, metallic bonding, brazing or bonding by species diffusion.

Claim 11 (Previously Presented): A method according to claim 18, further comprising healing annealing of the implantation defects on the thin film.

Claim 12 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out before the thinning.

Claim 13 (Previously Presented): A method according to claim 11, wherein the healing annealing is carried out after the thinning.

Claims 14-17 (Canceled).

Claim 18 (Previously Presented): A method for transferring an electrically active SiC thin layer from an initial SiC substrate, the method comprising:

determining hydrogen ion implantation conditions including dose, energy and implantation current that create a buried, embrittled film at a depth, with respect to an implanted face of the initial SiC substrate, wherein an implantation defect concentration in a

first 500 nm of implanted SiC is lower than 9.10^{20} atoms/cm³, and a number of acceptor defects compatible with desired electrical properties of an active thin layer is obtained;

performing hydrogen ion implantation through a face of the initial SiC substrate, under said determined hydrogen ion implantation conditions, and creating said buried, embrittled film;

fastening the face of the initial SiC substrate after implantation to a face of a target substrate, to obtain a structure;

separating the structure in two parts at a level of the buried embrittled film; and

thinning a layer of the SiC remaining fastened to the target substrate to a thickness lower than 500 nm.

Claim 19 (New). The method of claim 18, wherein the performing hydrogen ion implantation creates said buried embrittled film at an average implantation depth greater than 1100 nm.

Claim 20 (New). The method of claim 19, wherein the thinning includes thinning the SiC remaining fastened to the target substrate with a thickness greater than 1100 nm to a thickness lower than 500 nm.

Claim 21 (New). The method of Claim 20, wherein the performing hydrogen ion implantation includes using an implantation energy of 180 keV.